

**Low Noise Silicon Bipolar RF Transistor**

- For low distortion amplifiers and oscillators up to 2 GHz at collector currents from 5 mA to 30 mA
- Pb-free (RoHS compliant) and halogen-free package with visible leads
- Qualification report according to AEC-Q101 available



**ESD (Electrostatic discharge) sensitive device, observe handling precaution!**

Type	Marking	Pin Configuration			Package
BFR93AW	R2s	1=B	2=E	3=C	SOT323

**Maximum Ratings** at  $T_A = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	12	V
Collector-emitter voltage	$V_{CES}$	20	
Collector-base voltage	$V_{CBO}$	20	
Emitter-base voltage	$V_{EBO}$	2	
Collector current	$I_C$	90	mA
Base current	$I_B$	9	
Total power dissipation <sup>1)</sup> $T_S \leq 108\text{ °C}$	$P_{tot}$	300	mW
Junction temperature	$T_J$	150	°C
Ambient temperature	$T_A$	-65 ... 150	
Storage temperature	$T_{Stg}$	-65 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>2)</sup>	$R_{thJS}$	140	K/W

<sup>1)</sup>  $T_S$  is measured on the collector lead at the soldering point to the pcb

<sup>2)</sup> For calculation of  $R_{thJS}$  please refer to Application Note AN077 (Thermal Resistance Calculation)

**Electrical Characteristics** at  $T_A = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	12	-	-	V
Collector-emitter cutoff current $V_{CE} = 20\text{ V}, V_{BE} = 0$	$I_{CES}$	-	-	100	$\mu\text{A}$
Collector-base cutoff current $V_{CB} = 10\text{ V}, I_E = 0$	$I_{CBO}$	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 2\text{ V}, I_C = 0$	$I_{EBO}$	-	-	10	$\mu\text{A}$
DC current gain $I_C = 30\text{ mA}, V_{CE} = 8\text{ V}, \text{ pulse measured}$	$h_{FE}$	70	100	140	-

**Electrical Characteristics at  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics (verified by random sampling)</b>					
Transition frequency $I_C = 30\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $f = 500\text{ MHz}$	$f_T$	4.5	6	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$ , $V_{BE} = 0$ , emitter grounded	$C_{cb}$	-	0.58	0.8	pF
Collector emitter capacitance $V_{CE} = 10\text{ V}$ , $f = 1\text{ MHz}$ , $V_{BE} = 0$ , base grounded	$C_{ce}$	-	0.3	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$ , $f = 1\text{ MHz}$ , $V_{CB} = 0$ , collector grounded	$C_{eb}$	-	1.9	-	
Minimum noise figure $I_C = 5\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ , $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$NF_{min}$	-	1.5	-	dB
Power gain, maximum available <sup>1)</sup> $I_C = 30\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ , $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$G_{ma}$	-	15.5	-	
Transducer gain $I_C = 30\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_L = 50\ \Omega$ , $f = 900\text{ MHz}$ $f = 1.8\text{ MHz}$	$ S_{21e} ^2$	-	13	-	dB
Third order intercept point at output <sup>2)</sup> $I_C = 30\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_L = 50\ \Omega$ , $f = 0.9\text{ GHz}$	$IP_3$	-	15	-	dBm
1dB Compression point $I_C = 30\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_L = 50\ \Omega$ , $f = 0.9\text{ GHz}$	$P_{-1dB}$	-	6	-	

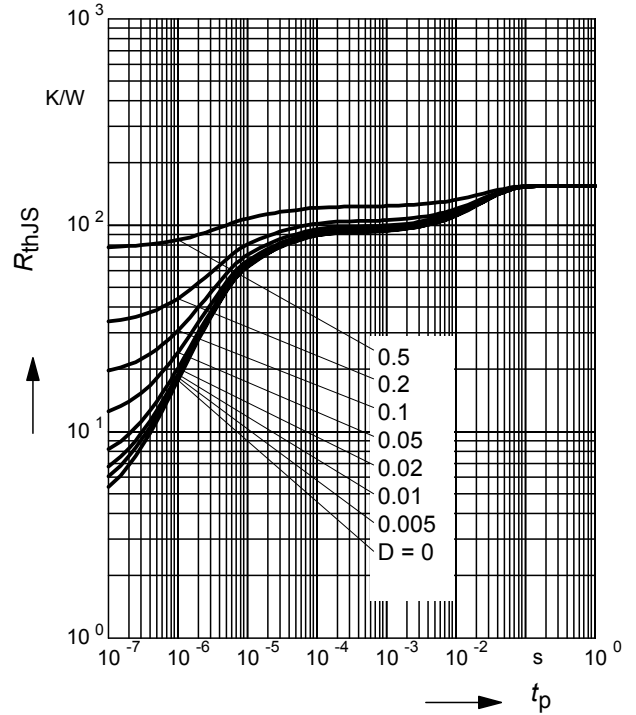
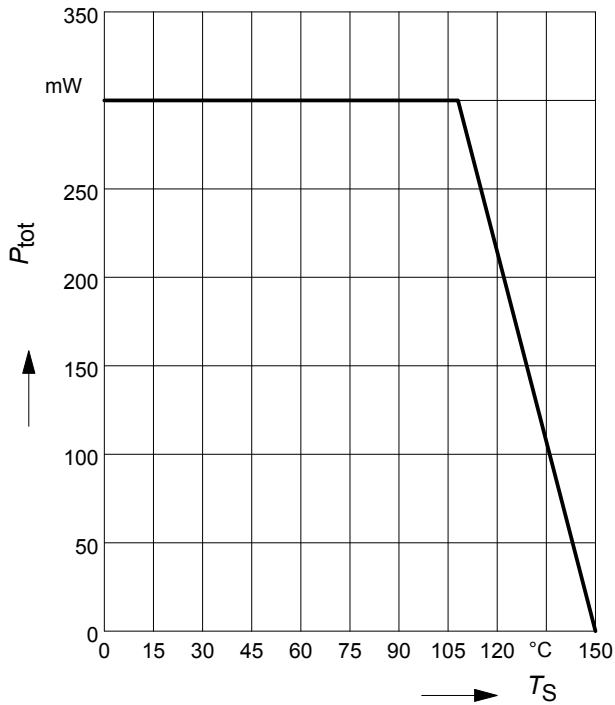
$$^1G_{ma} = |S_{21e} / S_{12e}| (k - (k^2 - 1)^{1/2})$$

<sup>2</sup>IP3 value depends on termination of all intermodulation frequency components.

Termination used for this measurement is 50Ω from 0.2 MHz to 12 GHz

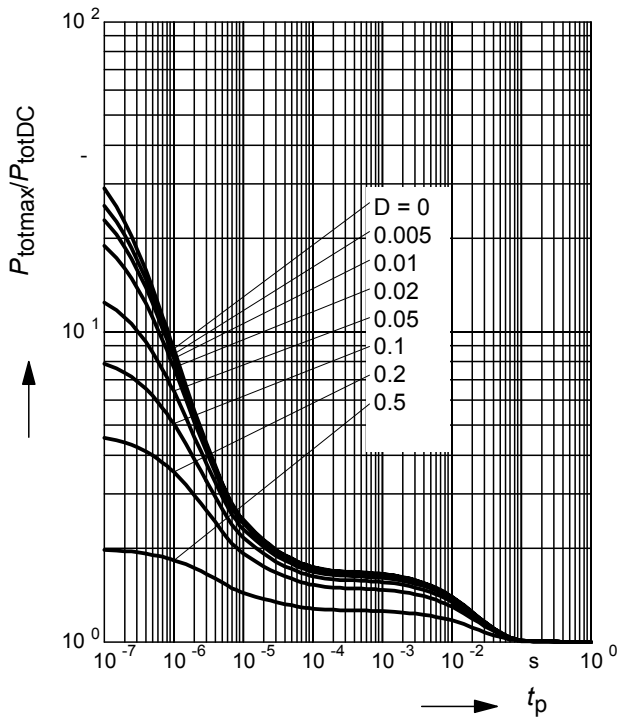
Total power dissipation  $P_{tot} = f(T_S)$

Permissible Pulse Load  $R_{thJS} = f(t_p)$

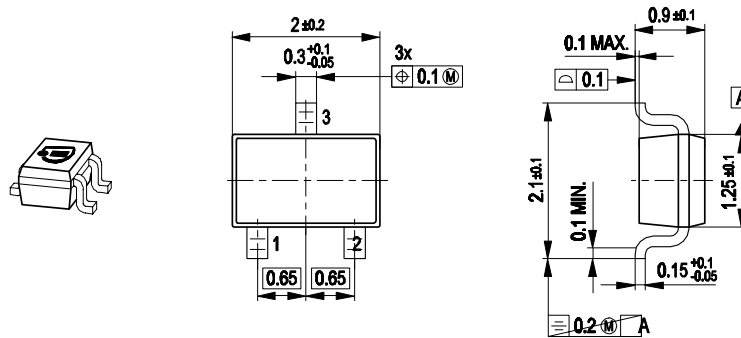


**Permissible Pulse Load**

$P_{totmax}/P_{totDC} = f(t_p)$



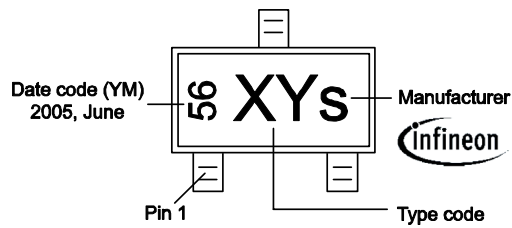
### Package Outline



### Foot Print

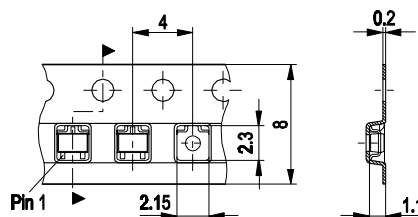


### Marking Layout (Example)



### Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel  
 Reel ø330 mm = 10.000 Pieces/Reel



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